# Triacs logic level

BT131 series

#### **GENERAL DESCRIPTION**

# Passivated, sensitive gate triacs in a plastic envelope, intended for use in general purpose bidirectional switching and phase control applications. These devices are intended to be interfaced directly to microcontrollers, logic integrated circuits and other low power gate

#### **QUICK REFERENCE DATA**

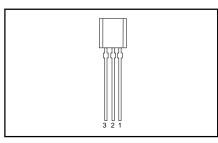
SYMBOL	PARAMETER	MAX.	MAX.	MAX.	UNIT
	BT131-	500	600	800	
V <sub>DRM</sub>	Repetitive peak off-state voltages RMS on-state current	500 1	600 1	800 1	V A
ITSM	Non-repetitive peak on-state current	16	16	16	Α

# **PINNING - TO92**

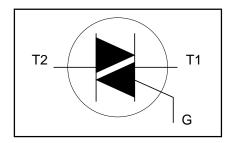
trigger circuits.

PIN	DESCRIPTION			
1	main terminal 2			
2	gate			
3	main terminal 1			

# **PIN CONFIGURATION**



## **SYMBOL**



### LIMITING VALUES

Limiting values in accordance with the Absolute Maximum System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.		UNIT	
$V_{DRM}$	Repetitive peak off-state voltages		-	<b>-500</b> 500 <sup>1</sup>	<b>-600</b> 600 <sup>1</sup>	<b>-800</b> 800	V
I <sub>T(RMS)</sub> I <sub>TSM</sub>	RMS on-state current Non-repetitive peak on-state current	full sine wave; T <sub>lead</sub> ≤51 °C full sine wave; T <sub>j</sub> = 25 °C prior to surge	-		1		A
		t = 20 ms t = 16.7 ms	-		16 17.6		A
l²t dl <sub>⊤</sub> /dt	I <sup>2</sup> t for fusing Repetitive rate of rise of on-state current after	t = 10.7  ms t = 10  ms $I_{TM} = 1.5 \text{ A}; I_{G} = 0.2 \text{ A};$ $dI_{G}/dt = 0.2 \text{ A}/\mu\text{s}$	-		1.28		A A <sup>2</sup> s
	triggering	T2+ G+ T2+ G- T2- G- T2- G+	- - -		50 50 50 10		A/μs A/μs A/μs A/μs
I <sub>GM</sub> V <sub>GM</sub> P <sub>GM</sub>	Peak gate current Peak gate voltage Peak gate power	12- 0+	- - -		2 5 5		Ανμs Α V W
PG(AV) Tstg Tj	Average gate power Storage temperature Operating junction temperature	over any 20 ms period	-40 -		0.5 150 125		Č C

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<sup>1</sup> Although not recommended, off-state voltages up to 800V may be applied without damage, but the triac may switch to the on-state. The rate of rise of current should not exceed 3 A/µs.

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# THERMAL RESISTANCES

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
R <sub>th j-lead</sub>	Thermal resistance	full cycle		-	60	K/W
R <sub>th j-a</sub>	junction to lead Thermal resistance junction to ambient	half cycle pcb mounted;lead length = 4mm	-	150	80 -	K/W K/W

# STATIC CHARACTERISTICS

T<sub>i</sub> = 25 °C unless otherwise stated

SYMBOL	PARAMETER	CONDITIONS		MIN.	TYP.	MAX.	UNIT
I <sub>GT</sub>	Gate trigger current	$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}$					
		T.	2+ G+	-	0.4	3	mΑ
		<u>-</u>	2+ G-	-	1.3	3 3	mΑ
			2- G-	-	1.4		mΑ
		<u>-</u>	2- G+	-	3.8	7	mΑ
I <sub>L</sub>	Latching current	$V_D = 12 \text{ V}; I_{GT} = 0.1 \text{ A}$					
			2+ G+	-	1.2	5	mΑ
			2+ G-	-	4.0	8 5 8 5	mΑ
		<u>-</u>	2- G-	-	1.0	5	mΑ
			2- G+	-	2.5	8	mΑ
l I <sub>H</sub>	Holding current	$V_D = 12 \text{ V}; I_{GT} = 0.1 \text{ A}$		-	1.3		mΑ
$V_{\text{T}}$	On-state voltage	$I_{T} = 2.0 \text{ A}$		-	1.2	1.5	V
V <sub>GT</sub>	Gate trigger voltage	$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}$		-	0.7	1.5	V
1.		$V_D = 400 \text{ V}; I_T = 0.1 \text{ A}; T_L = 125 ^{\circ}\text{C}$	;	0.2	0.3		V
$I_D$	Off-state leakage current	$V_D = V_{DRM(max)}$ , $T_j = 125 °C$		-	0.1	0.5	mA

# **DYNAMIC CHARACTERISTICS**

 $T_i = 25$  °C unless otherwise stated

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
dV <sub>D</sub> /dt	Critical rate of rise of	$V_{DM} = 67\% V_{DRM(max)}; T_j = 125 \text{ °C};$	5	15	-	V/μs
t <sub>gt</sub>	off-state voltage Gate controlled turn-on time	exponential waveform, $R_{GK} = 1 \text{ k}\Omega$ $I_{TM} = 1.5 \text{ A}$ ; $V_D = V_{DRM(max)}$ ; $I_G = 0.1 \text{ A}$ ; $dI_G/dt = 5 \text{ A}/\mu\text{s}$	-	2	-	μs

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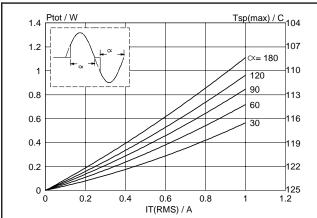


Fig.1. Maximum on-state dissipation,  $P_{tot}$ , versus rms on-state current,  $I_{T(RMS)}$ , where  $\alpha =$  conduction angle.

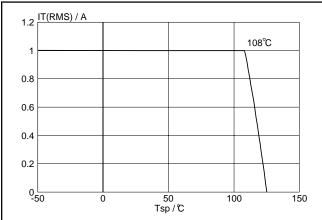


Fig.4. Maximum permissible rms current  $I_{T(RMS)}$ , versus lead temperature  $T_{lead}$ .

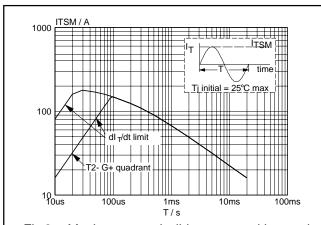


Fig.2. Maximum permissible non-repetitive peak on-state current  $I_{TSM}$ , versus pulse width  $t_p$ , for sinusoidal currents,  $t_p \le 20$ ms.

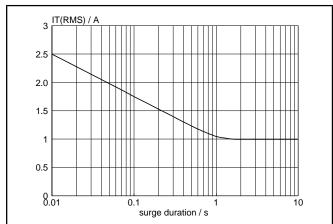


Fig.5. Maximum permissible repetitive rms on-state current  $I_{T(RMS)}$ , versus surge duration, for sinusoidal currents, f = 50 Hz;  $T_{lead} \le 51$  °C.

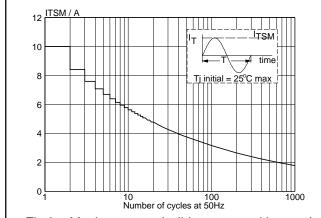


Fig.3. Maximum permissible non-repetitive peak on-state current  $I_{TSM}$ , versus number of cycles, for sinusoidal currents, f = 50 Hz.

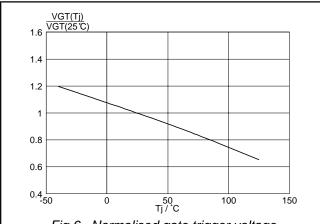
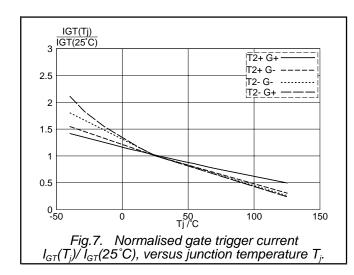


Fig.6. Normalised gate trigger voltage  $V_{GT}(T_j)/V_{GT}(25^{\circ}C)$ , versus junction temperature  $T_j$ .

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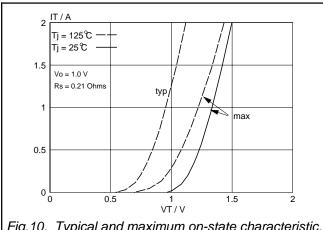


Fig. 10. Typical and maximum on-state characteristic.

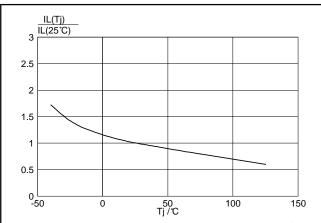


Fig.8. Normalised latching current  $I_L(T_j)/I_L(25^{\circ}\text{C})$ , versus junction temperature  $T_j$ .

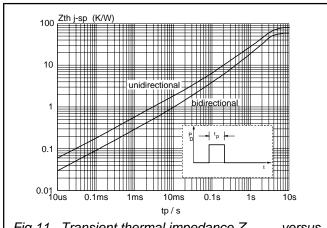


Fig.11. Transient thermal impedance  $Z_{th i-lead}$ , versus pulse width  $t_{\rm p}$ .

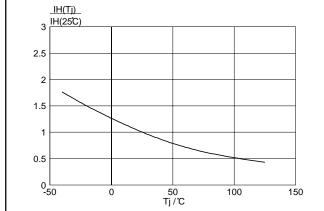


Fig.9. Normalised holding current  $I_H(T_i)/I_H(25^{\circ}\text{C})$ , versus junction temperature  $T_j$ .

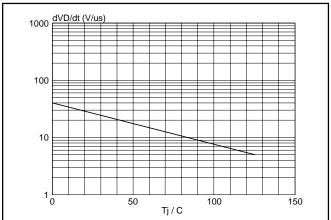
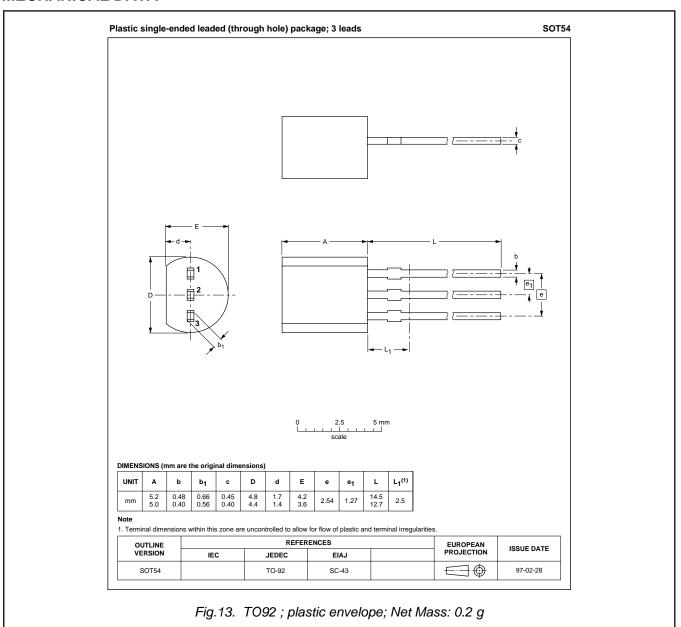


Fig.12. Typical, critical rate of rise of off-state voltage,  $dV_D/dt$  versus junction temperature  $T_{j\cdot}$ 

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# **MECHANICAL DATA**



#### Notes

1. Epoxy meets UL94 V0 at 1/8".

Philips Semiconductors Product specification

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#### **DEFINITIONS**

Data sheet status					
Objective specification This data sheet contains target or goal specifications for product development.					
Preliminary specification	This data sheet contains preliminary data; supplementary data may be published later.				
Product specification This data sheet contains final product specifications.					
1					

#### Limiting values

Limiting values are given in accordance with the Absolute Maximum Rating System (IEC 134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of this specification is not implied. Exposure to limiting values for extended periods may affect device reliability.

#### **Application information**

Where application information is given, it is advisory and does not form part of the specification.

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